

Title (en)
DIE PACKAGE WITH SUPERPOSER SUBSTRATE FOR PASSIVE COMPONENTS

Title (de)
CHIPVERPACKUNG MIT ÜBERGELAGERTEM SUBSTRAT FÜR PASSIVE BAUELEMENTE

Title (fr)
CONDITIONNEMENT DE PUCE À SUBSTRAT SUPERPOSEUR POUR COMPOSANTS PASSIFS

Publication
EP 3050098 A4 20170510 (EN)

Application
EP 13894760 A 20130927

Priority
US 2013062388 W 20130927

Abstract (en)
[origin: WO2015047330A1] A die package is described that includes a substrate to carry passive components. In one example, the package has a semiconductor die having active circuitry near a front side of the die and having a back side opposite the front side, and a component substrate near the back side of the die. A plurality of passive electrical components are on the component substrate and a conductive path connects a passive component to the active circuitry. The die has a silicon substrate between the front side and the back side and the conductive path is a through-silicon via through the die from the back side to the active circuit.

IPC 8 full level
H01L 23/48 (2006.01); **H01L 23/498** (2006.01); **H01L 23/538** (2006.01); **H01L 23/66** (2006.01); **H01L 25/00** (2006.01); **H01L 25/065** (2006.01); **H01L 25/16** (2006.01)

CPC (source: EP GB KR US)
H01L 23/481 (2013.01 - EP GB KR US); **H01L 23/49822** (2013.01 - EP GB KR US); **H01L 23/49827** (2013.01 - EP GB KR US); **H01L 23/49833** (2013.01 - EP GB KR US); **H01L 23/5226** (2013.01 - GB); **H01L 23/5389** (2013.01 - EP GB KR US); **H01L 23/58** (2013.01 - GB); **H01L 23/66** (2013.01 - EP GB KR US); **H01L 25/0657** (2013.01 - EP GB KR US); **H01L 25/16** (2013.01 - EP KR US); **H01L 25/162** (2013.01 - GB); **H01L 25/50** (2013.01 - GB US); **H01L 2223/6616** (2013.01 - US); **H01L 2223/6655** (2013.01 - US); **H01L 2223/6672** (2013.01 - US); **H01L 2224/16225** (2013.01 - EP KR US); **H01L 2224/16265** (2013.01 - EP US); **H01L 2225/06517** (2013.01 - EP KR US); **H01L 2225/0652** (2013.01 - US); **H01L 2225/06544** (2013.01 - US); **H01L 2225/06555** (2013.01 - US); **H01L 2225/06572** (2013.01 - EP KR US); **H01L 2225/06582** (2013.01 - US)

Citation (search report)

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Designated contracting state (EPC)
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

DOCDB simple family (publication)
DE 202014104574 U1 20141113; CN 104517953 A 20150415; CN 104517953 B 20181218; EP 3050098 A1 20160803; EP 3050098 A4 20170510; EP 3050098 B1 20210519; GB 201416330 D0 20141029; GB 2520149 A 20150513; GB 2520149 B 20180516; JP 2016528735 A 20160915; JP 6464435 B2 20190206; KR 102052294 B1 20191204; KR 20160036666 A 20160404; KR 20180120814 A 20181106; TW 201519379 A 20150516; TW 201731041 A 20170901; TW I575675 B 20170321; TW I671866 B 20190911; US 10615133 B2 20200407; US 2016181211 A1 20160623; WO 2015047330 A1 20150402

DOCDB simple family (application)
DE 202014104574 U 20140924; CN 201410502983 A 20140926; EP 13894760 A 20130927; GB 201416330 A 20140916; JP 2016534570 A 20130927; KR 20167005077 A 20130927; KR 20187031416 A 20130927; TW 103132645 A 20140922; TW 105143413 A 20140922; US 2013062388 W 20130927; US 201314910606 A 20130927